

Data Sheet No. PD60032 rev P

### IR2131(J)(S) & (PbF)

#### **Features**

- Floating channel designed for bootstrap operation Fully operational to +600V Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for all channels
- Over-current shutdown turns off all six drivers
- Independent 3 high side & 3 low side drivers
- Matched propagation delay for all channels
- 2.5V logic compatible
- Outputs out of phase with inputs
- 28-Lead SOIC & 44-Lead PLCC are also available in Lead-Free.

#### Description

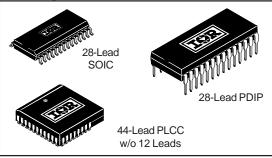
The IR2131(J)(S) is a high voltage, high speed power MOSFET and IGBT driver with three independent high and low side referenced output channels. Proprietary HVIC technology enables ruggedized monolithic construction. Logic inputs are compatible with CMOS or LSTTL outputs, down to 2.5V logic. A current trip function which terminates all six outputs can be derived from an external current sense resistor. A shutdown input is provided for a customized shutdown function. An open drain FAULT signal is provided to indicate that any of the shutdowns has occurred. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channels can be used to drive N-channel power MOSFETs or IGBTs in the high side configuration which operate up to 600 volts.

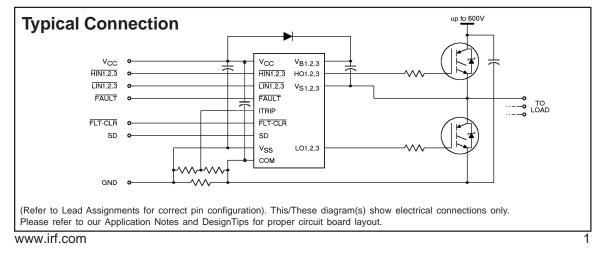
#### Product Summary

**3 HIGH SIDE AND 3 LOW SIDE DRIVER** 

VOFFSET	600V max.
I <sub>O</sub> +/-	160 mA / 360 mA
Vout	10 - 20V
ton/off (typ.)	1.3 & 0.6 µs

#### Packages





#### **Absolute Maximum Ratings**

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions. Additional Information is shown in Figures 7 through 10.

Symbol	Definition		Min.	Max.	Units
V <sub>B1,2,3</sub>	High Side Floating Supply Voltage	-0.3	625		
V <sub>S1,2,3</sub>	High Side Floating Offset Voltage		V <sub>B1,2,3</sub> - 25	V <sub>B1,2,3</sub> + 0.3	
V <sub>HO1,2,3</sub>	High Side Floating Output Voltage	V <sub>S1,2,3</sub> - 0.3	V <sub>B1,2,3</sub> + 0.3		
V <sub>CC</sub>	Low Side and Logic Fixed Supply Voltage		-0.3	25	
V <sub>SS</sub>	Logic Ground		V <sub>CC</sub> - 25	V <sub>CC</sub> + 0.3	
V <sub>LO1,2,3</sub>	Low Side Output Voltage		-0.3	V <sub>CC</sub> + 0.3	V
V <sub>IN</sub>	Logic Input Voltage (HIN1,2,3, LIN1,2,3, FL	T-CLR, SD&ITRIP)	V <sub>SS</sub> - 0.3	(V <sub>SS</sub> + 15) or	
				(V <sub>CC</sub> + 0.3) whichever	
				is lower	
V <sub>FLT</sub>	FAULT Output Voltage		V <sub>SS</sub> - 0.3	V <sub>CC</sub> + 0.3	
dV <sub>S</sub> /dt	Allowable Offset Supply Voltage Transient			50	V/ns
PD	Package Power Dissipation @ $T_A \le +25^{\circ}C$	(28 Lead DIP)		1.5	
		(28 Lead SOIC)	—	1.6	W
		(44 Lead PLCC)	—	2.0	
Rth <sub>JA</sub>	Thermal Resistance, Junction to Ambient	(28 Lead DIP)	—	83	
		(28 Lead SOIC)	—	78	°C/W
		(44 Lead PLCC)	_	63	°C
TJ	Junction Temperature		_	150	
T <sub>S</sub>	Storage Temperature		-55	150	
TL	Lead Temperature (Soldering, 10 seconds)			300	

### **Recommended Operating Conditions**

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to COM. The V<sub>S</sub> offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V <sub>B1,2,3</sub>	High Side Floating Supply Voltage	V <sub>S1,2,3</sub> + 10	V <sub>S1,2,3</sub> + 20	
V <sub>S1,2,3</sub>	High Side Floating Offset Voltage	Note 1	600	
V <sub>HO1,2,3</sub>	High Side Floating Output Voltage	V <sub>S1,2,3</sub>	V <sub>B1,2,3</sub>	
V <sub>CC</sub>	Low Side and Logic Fixed Supply Voltage	10	20	V
V <sub>SS</sub>	Logic Ground	-5	5	v
V <sub>LO1,2,3</sub>	Low Side Output Voltage	0	V <sub>CC</sub>	
V <sub>IN</sub>	Logic Input Voltage (HIN1,2,3, LIN1,2,3, FLT - CLR, SD & ITRIP)	V <sub>SS</sub>	V <sub>SS</sub> + 5	
V <sub>FLT</sub>	FAULT Output Voltage	V <sub>SS</sub>	V <sub>CC</sub>	
T <sub>A</sub>	Ambient Temperature	-40	125	°C

Note 1: Logic operational for  $V_S$  of -5V to +600V. Logic state held for  $V_S$  of -5V to - $V_{BS}$ . (Please refer to the Design Tip DT97-3 for more details).

Note 2: All input pins, CA- and CAO pins are internally clamped with a 5.2V zener diode.

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### **Dynamic Electrical Characteristics**

 $V_{BIAS}$  (V<sub>CC</sub>, V<sub>BS1,2,3</sub>) = 15V, V<sub>S1,2,3</sub> = V<sub>SS</sub> = COM, C<sub>L</sub> = 1000 pF and T<sub>A</sub> = 25°C unless otherwise specified. The dynamic electrical characteristics are defined in Figures 4 through 5.

Parameter Value						
Symbol	Definition	Min.	Min.   Typ.   Max.			Test Conditions
t <sub>on</sub>	Turn-On Propagation Delay	0.6	1.3	2.0	μs	
t <sub>off</sub>	Turn-Off Propagation Delay	0.2	0.6	1.0	μο	V <sub>IN</sub> = 0 & 5V
tr	Turn-On Rise Time	—	80	150		V <sub>S1,2,3</sub> = 0 to 600V
t <sub>f</sub>	Turn-Off Fall Time	—	40	100		
t <sub>itrip</sub>	ITRIP to Output Shutdown Propagation Delay	400	700	1000		V <sub>IN</sub> , V <sub>ITRIP</sub> = 0 & 5V
t <sub>bl</sub>	ITRIP Blanking Time	—	400	—		V <sub>ITRIP</sub> = 1V
t <sub>flt</sub>	ITRIP to FAULT Indication Delay	400	700	1000	ns	V <sub>IN</sub> , V <sub>ITRIP</sub> = 0 & 5V
t <sub>flt,in</sub>	Input Filter Time (All Six Inputs)	—	310	—		V <sub>IN</sub> = 0 & 5V
t <sub>fltclr</sub>	FLT-CLR to FAULT Clear Time	400	800	1200		V <sub>IN</sub> , V <sub>IT</sub> , V <sub>FC</sub> = 0&5V
t <sub>sd</sub>	SD to Output Shutdown Propagation Delay	400	700	1000		V <sub>IN</sub> , V <sub>SD</sub> = 0 & 5V

NOTE: For high side PWM, HIN pulse width must be  $\geq 1.5 \mu$ sec

### **Static Electrical Characteristics**

 $V_{BIAS}$  (V<sub>CC</sub>,  $V_{BS1,2,3}$ ) = 15V,  $V_{S1,2,3}$  =  $V_{SS}$  = COM and  $T_A$  = 25°C unless otherwise specified. The  $V_{IN}$ ,  $V_{TH}$  and  $I_{IN}$  parameters are referenced to  $V_{SS}$  and are applicable to all six logic input leads: HIN1,2,3 & LIN1,2,3 . The  $V_O$  and  $I_O$  parameters are referenced to COM and  $V_{S1,2,3}$  and are applicable to the respective output leads: HO1,2,3 or LO1,2,3.

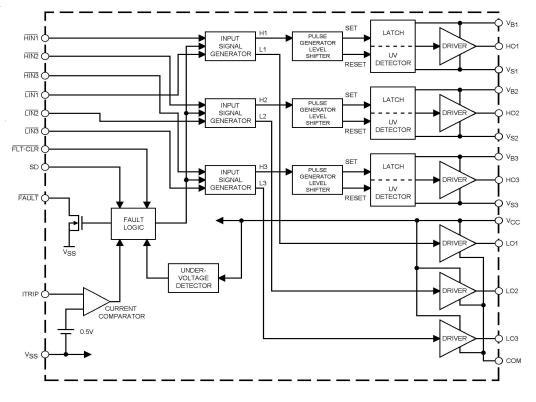
	Parameter Value					
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
VIH	Logic "0" Input Voltage (OUT = LO)	2.2	_	_		
V <sub>IL</sub>	Logic "1" Input Voltage (OUT = HI)	-	_	0.8		
V <sub>FCLR</sub> ,IH	Logic "0" Fault Clear Input Voltage	2.2	—	—	V	
V <sub>FCLR,IL</sub>	Logic "1" Fault Clear Input Voltage	—	—	0.8	v	
V <sub>SD,TH+</sub>	Shutdown Input Positive Going Threshold	1.2	1.8	2.1		
V <sub>SD,TH-</sub>	Shutdown Input Negative Going Threshold	0.9	1.5	1.8		
V <sub>IT,TH+</sub>	ITRIP Input Positive Going Threshold	250	485	600		
V <sub>IT,TH-</sub>	ITRIP Input Negative Going Threshold	200	400	550	mV	
VOH	High Level Output Voltage, V <sub>BIAS</sub> - VO	-	—	100	IIIV	$V_{IN} = 0V, I_O = 0A$
V <sub>OL</sub>	Low Level Output Voltage, VO	_	_	100		$V_{IN} = 5V, I_O = 0A$
I <sub>LK</sub>	Offset Supply Leakage Current	—	—	50	μA	$V_B = V_S = 600V$
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Supply Current	—	30	100	μΑ	$V_{IN} = 0V \text{ or } 5V$
I <sub>QCC</sub>	Quiescent V <sub>CC</sub> Supply Current	—	3.0	4.5	mA	$V_{IN} = 0V \text{ or } 5V$
I <sub>IN+</sub>	Logic "1" Input Bias Current (OUT = HI)	—	190	300		$V_{IN} = 0V$
I <sub>IN-</sub>	Logic "0" Input Bias Current (OUT = LO)	-	50	100	μA	$V_{IN} = 5V$
I <sub>ITRIP+</sub>	"High" ITRIP Bias Current	_	75	150		ITRIP = 5V
I <sub>ITRIP-</sub>	"Low" ITRIP Bias Current	_	_	100	nA	ITRIP = 0V
I <sub>FCLR+</sub>	Logic "1" Fault Clear Bias Current	—	125	250		$\overline{FLT} - CLR = 0V$
I <sub>FCLR-</sub>	Logic "0" Fault Clear Bias Current	_	75	150	μA	$\overline{FLT} - CLR = 5V$
I <sub>SD+</sub>	Logic "1" Shutdown Bias Current	—	75	150		SD = 5V
I <sub>SD-</sub>	Logic "0" Shutdown Bias Current	—	_	100	nA	SD = 0V

### **Static Electrical Characteristics -- Continued**

 $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS1,2,3}$ ) = 15V,  $V_{S1,2,3}$  =  $V_{SS}$  = COM and  $T_A$  = 25°C unless otherwise specified. The  $V_{IN}$ ,  $V_{TH}$  and  $I_{IN}$  parameters are referenced to  $V_{SS}$  and are applicable to all six logic input leads: HIN1,2,3 & LIN1,2,3 . The  $V_O$  and  $I_O$  parameters are referenced to COM and  $V_{S1,2,3}$  and are applicable to the respective output leads: HO1,2,3 or LO1,2,3.

Parameter				Value		
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V <sub>BSUV+</sub>	V <sub>BS</sub> Supply Undervoltage Positive Going Threshold	8.2	8.7	9.2		
V <sub>BSUV-</sub>	V <sub>BS</sub> Supply Undervoltage Negative Going Threshold	7.8	8.3	8.8	V	
V <sub>CCUV+</sub>	V <sub>CC</sub> Supply Undervoltage Positive Going Threshold	8.2	8.7	9.2	V	
V <sub>CCUV-</sub>	V <sub>CC</sub> Supply Undervoltage Negative Going Threshold	7.8	8.3	8.8		
R <sub>on,FLT</sub>	FAULT Low On-Resistance		55	75	Ω	
I <sub>O+</sub>	Output High Short Circuit Pulsed Current	160	250	—	mA	$V_O = 0V, V_{IN} = 0V$ PW $\leq 10 \ \mu s$
I <sub>O-</sub>	Output Low Short Circuit Pulsed Current	360	500	_	mA	$V_{O}$ = 15V, $V_{IN}$ = 5V PW $\leq$ 10 µs

### **Functional Block Diagram**



### International **100** Rectifier

# IR2131(J)(S) & (PbF)

### **Lead Definitions**

Lea	ad
Symbol	Description
HIN1,2,3	Logic inputs for high side gate driver outputs (HO1,2,3), out of phase
LIN1,2,3	Logic inputs for low side gate driver output (LO1,2,3), out of phase
FLT-CLR	Logic input for fault clear
SD	Logic input for shutdown
FAULT	Indicates over-current or undervoltage lockout (low side) has occurred, negative logic
Vcc	Low side and logic fixed supply
ITRIP	Input for over-current shutdown
V <sub>SS</sub>	Logic ground
VB1,2,3	High side floating supplies
HO1,2,3	High side gate drive outputs
V <sub>S1,2,3</sub>	High side floating supply returns
LO1,2,3	Low side gate drive outputs
COM	Low side return

### Lead Assignments

8 FAULT 21 FAULT 21   9 ITRIP VB3 20 III   10 FLT-CLR H03 19 III   11 SD VS3 18 III SD VS3 18   12 VSS 17 FLT-CLR III SD VS3 18   12 VSS 17 FLT-CLR III SD VS3 18   11 COM LO1 IE III SD VS3 18   14 LO3 LO2 IS III III SD VS3 16   III SD VS3 IS III SD VS3 18   III COM LO1 IE IIII SD VS3 18   IIII COM LO1 IE IIII IIII SD VS3 11   IIII COM LO1 IE IIII IIII IIII IIIII IIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIII
28 Lead DIP   44 Lead PLCC w/o 12 Leads   28 Lead SOIC (Wide Body)     IR2131   IR2131J   IR2131S
Part Number

International

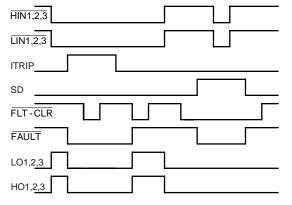


Figure 1. Input/Output Timing Diagram

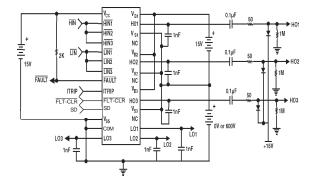


Figure 3. Switching Time Test Circuit

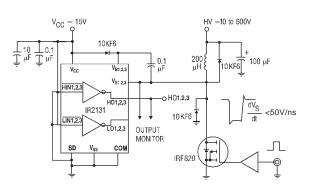


Figure 2. Floating Supply Voltage Transient Test Circuit

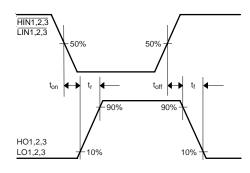


Figure 4. Switching Time Waveform Definitions

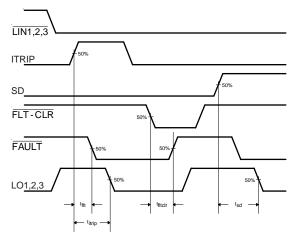
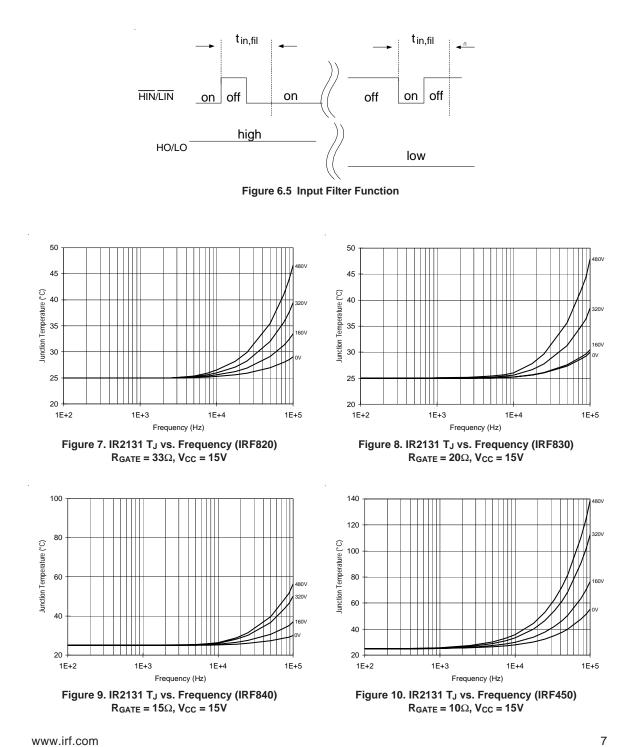
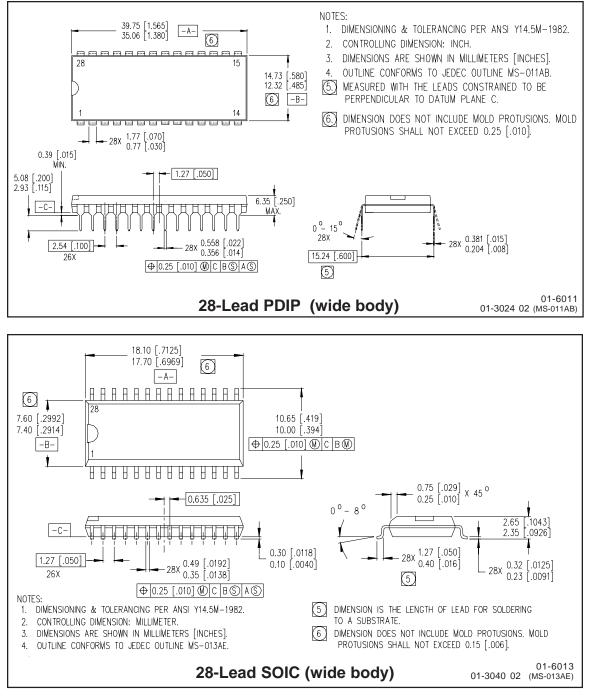


Figure 6. Shutdown Waveform Definitions

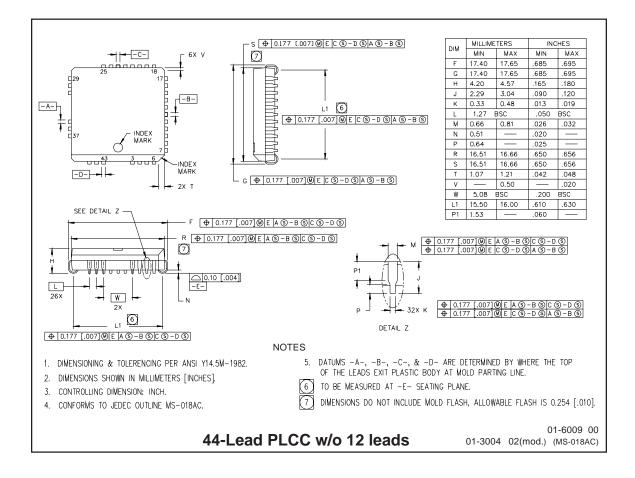
### International **TOR** Rectifier



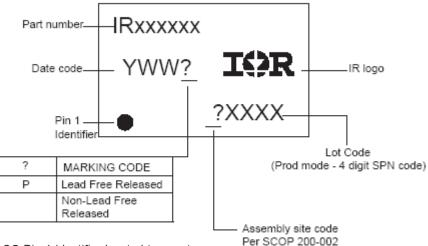
#### **Case outlines**



International **ISPR** Rectifier



### LEADFREE PART MARKING INFORMATION



\* PLCC Pin 1 identifier located top center

#### **ORDER INFORMATION**

Basic Part (Non-L	ead Free)		Lead-Free Part		
28-Lead PDIP	IR2131	order IR2131	28-Lead PDIP	IR2131	order Not available
28-Lead SOIC	IR2131S	order IR2131S	28-Lead SOIC	IR2131S	order IR2131SPbF
44-Lead PLCC	IR2131J	order IR2131J	44-Lead PLCC	IR2131J	order IR2131JPbF

# International

This product has been designed and qualified for the Industrial market. Qualification Standards can be found on IR's Web site. Data and specifications subject to change without notice. IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105 TAC Fax: (310) 252-7903 Visit us at www.irf.com for sales contact information. 10/11/04

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